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SB360 SCHOTTKY RECTIFIER

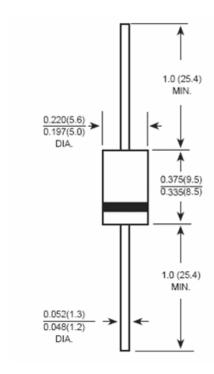
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



DO-201AD

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Marking Diagram:





SB = Device Type
3 = Forward Current (3A)
60 = Reverse Voltage (60V)
SSG = SSG
YY = Year

YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB360	DO-201AD	1250 pag / Tapa
	(Pb-Free)	1250 pcs / Tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @TC = 80 °C rectangular wave form(L=0.375")	3.0	А
Max. Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	80	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 3A, Pulse, T _J = 25°C	0.74	V
Max. Reverse Current	I _{R1}	$@V_R = \text{rated VR}$ $T_J = 25^{\circ}C$	0.5	mA
	I _{R2}	$@V_R = \text{rated VR}$ $T_J = 100^{\circ}C$	20	mA
Typical Junction Capacitance	Cj	$@V_R = 4.0 \text{ V, Tc=}25^{\circ}\text{C}$ $f_{SIG} = 1\text{MHz}$	250	pF

^{*} Pulse Width < 300µs, Duty Cycle <2%

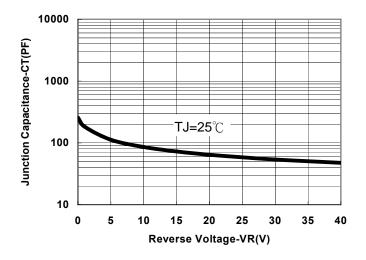
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^{\circ}\mathbb{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\mathbb{C}$
Maximum Thermal Resistance Junction to Case	$R_{ ext{ heta}JC}$	DC operation	8	°C/W
Approximate Weight	wt	-	1.02	g
Case Style		DO-201AD		

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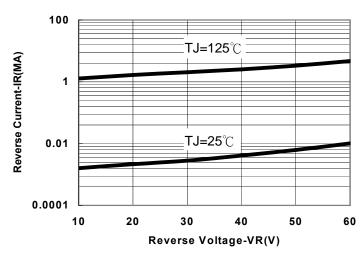


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

Fig.2-Typical Values Of Reverse Current VS.Reverse Voltage

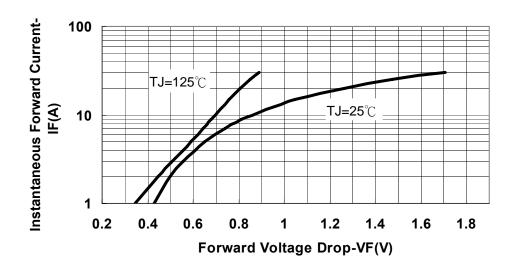


Fig.3-Typical Forward Voltage Drop Characteristics

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Technical Data Data Sheet N0086, Rev. -

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